

GJ9960**N-CHANNEL ENHANCEMENT MODE POWER MOSFET**

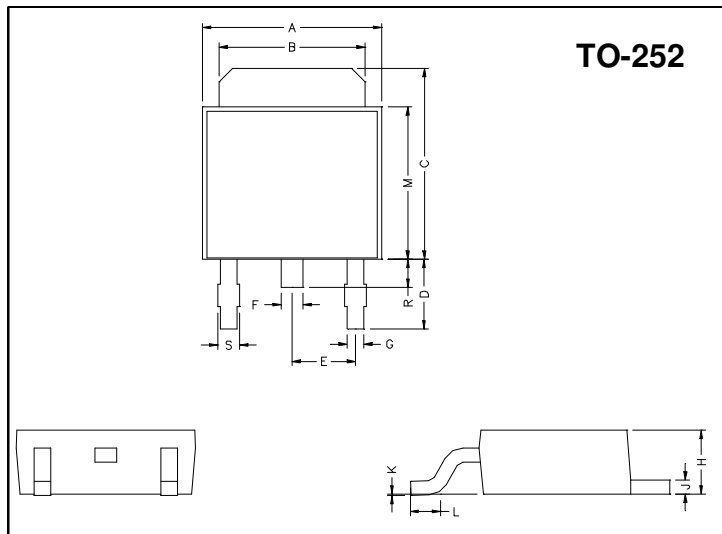
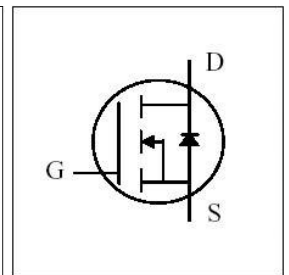
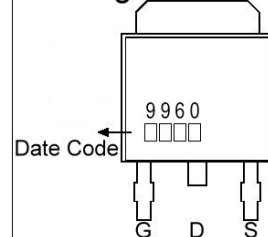
BV _{DSS}	40V
R _{DS(ON)}	16mΩ
I _D	42A

Description

The GJ9960 provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

Features

- *Simple Drive Requirement
- *Low Gate Charge
- *Fast Switching

Package Dimensions**Marking :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current, V _{GS} @10V	I _D @T _C =25°C	42	A
Continuous Drain Current, V _{GS} @10V	I _D @T _C =100°C	26	A
Pulsed Drain Current ¹	I _{DM}	195	A
Total Power Dissipation	P _D @T _C =25°C	45	W
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55 ~ +150	°C
Linear Derating Factor		0.36	W/°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	R _{thj-c}	2.8	°C/W
Thermal Resistance Junction-ambient Max.	R _{thj-a}	110	°C/W

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	40	-	-	V	V _{GS} =0, I _D =250uA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.032	-	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} =V _{GS} , I _D =250uA
Forward Transconductance	g _{fs}	-	30	-	S	V _{DS} =10V, I _D =20A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	1	uA	V _{DS} =40V, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		-	-	25	uA	V _{DS} =32V, V _{GS} =0
Static Drain-Source On-Resistance	R _{DS(on)}	-	-	16	mΩ	I _D =20A, V _{GS} =10V
		-	-	25		I _D =18A, V _{GS} =4.5V
Total Gate Charge ²	Q _g	-	18	-	nC	I _D =20A V _{DS} =20V V _{GS} =4.5V
Gate-Source Charge	Q _{gs}	-	6	-		
Gate-Drain ("Miller") Change	Q _{gd}	-	12	-		
Turn-on Delay Time ²	T _{d(on)}	-	9	-	ns	V _{DS} =20V I _D =20A V _{GS} =10V R _G =3.3Ω R _D =1Ω
Rise Time	T _r	-	110	-		
Turn-off Delay Time	T _{d(off)}	-	23	-		
Fall Time	T _f	-	10	-		
Input Capacitance	C _{iss}	-	1500	-	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	-	250	-		
Reverse Transfer Capacitance	C _{rss}	-	180	-		

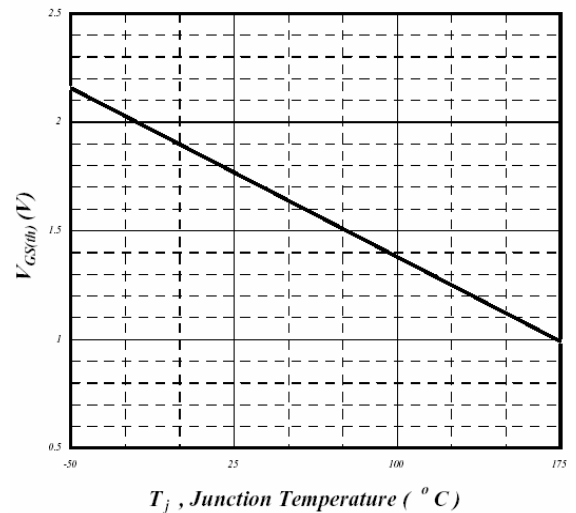
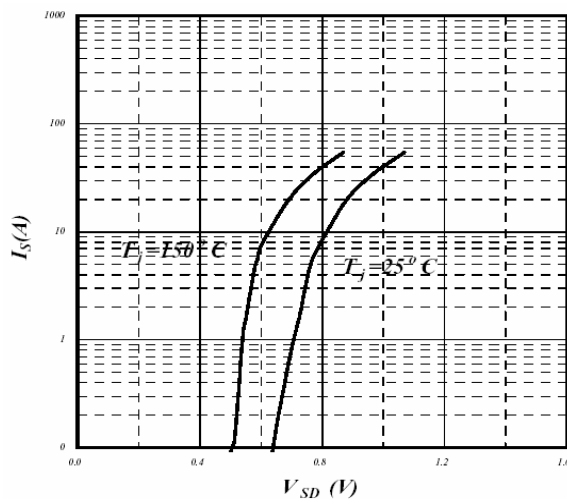
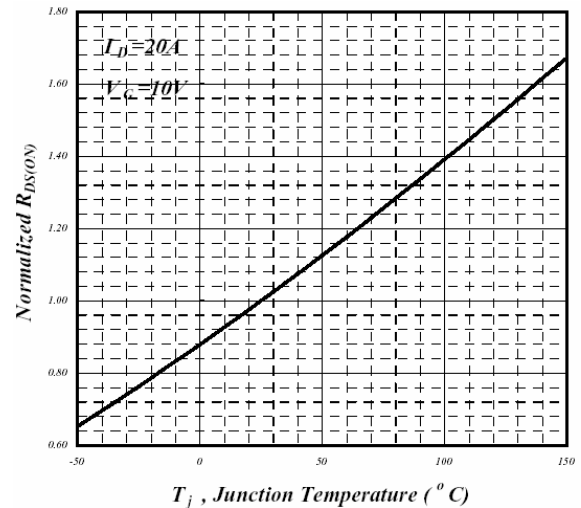
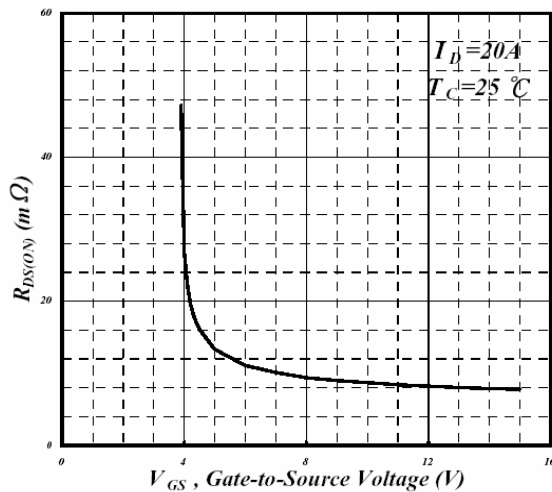
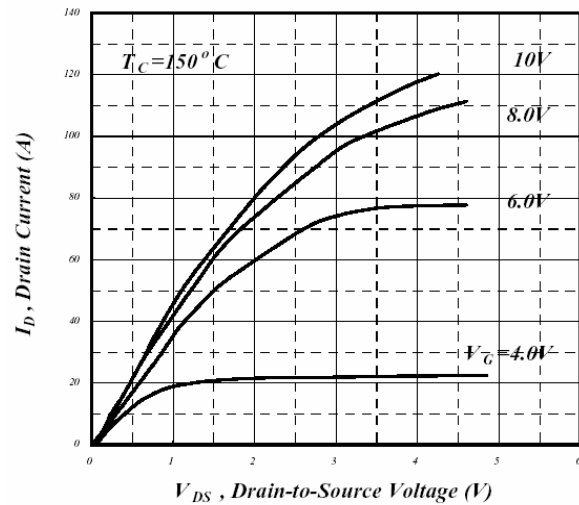
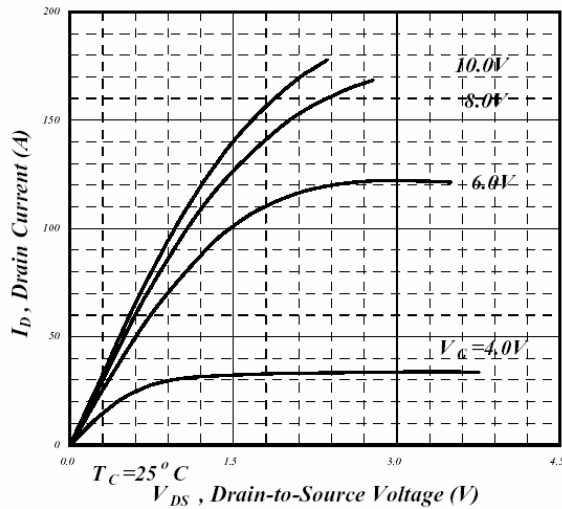
Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	1.3	V	I _S =45A, V _{GS} =0V
Reverse Recovery Time	T _{rr}	-	22	-	ns	I _S =20A, V _{GS} =0V dI/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	27.4	-	nC	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

Characteristics Curve



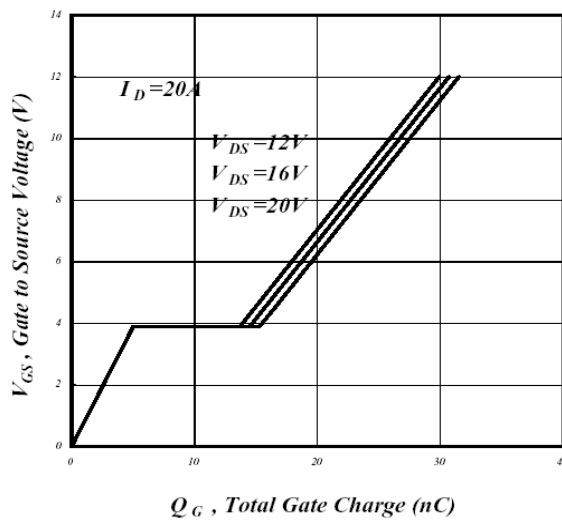


Fig 7. Gate Charge Characteristics

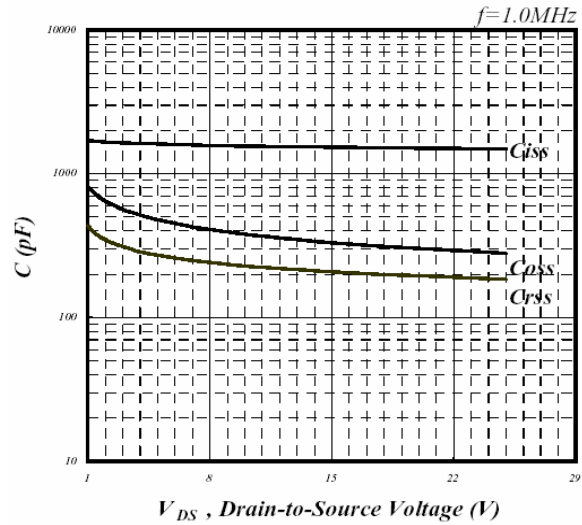


Fig 8. Typical Capacitance Characteristics

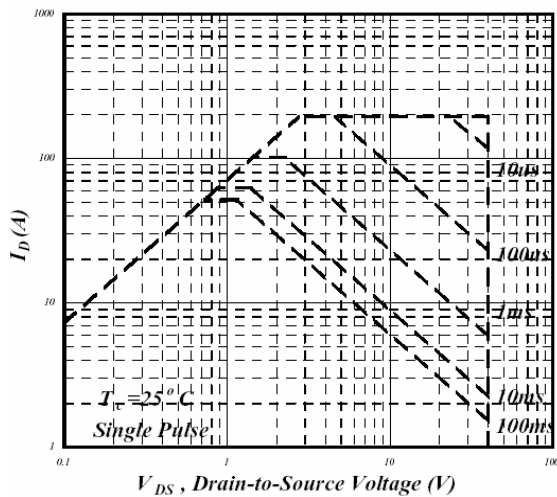


Fig 9. Maximum Safe Operating Area

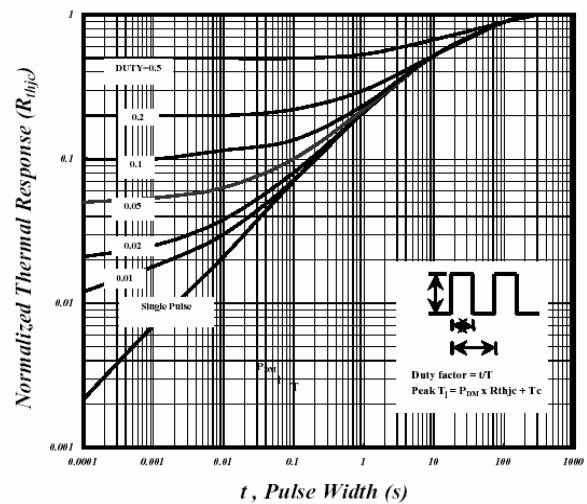


Fig 10. Effective Transient Thermal Impedance

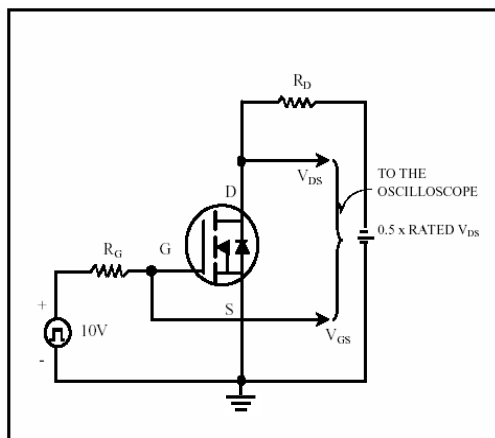


Fig 11. Switching Time Circuit

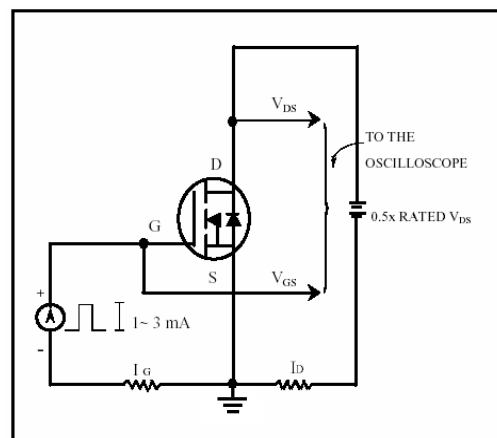


Fig 12. Gate Charge Circuit

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Head Office And Factory:

- Taiwan: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- China: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165